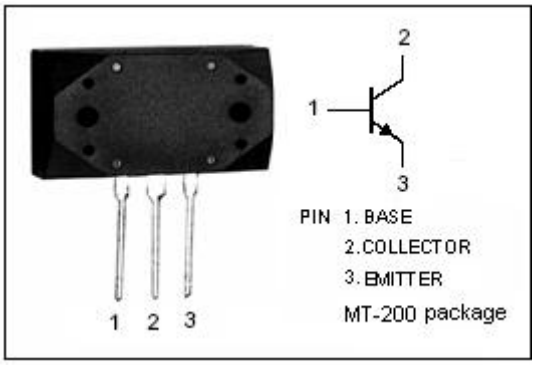
isc Silicon NPN Power Transistor — 2SC3264

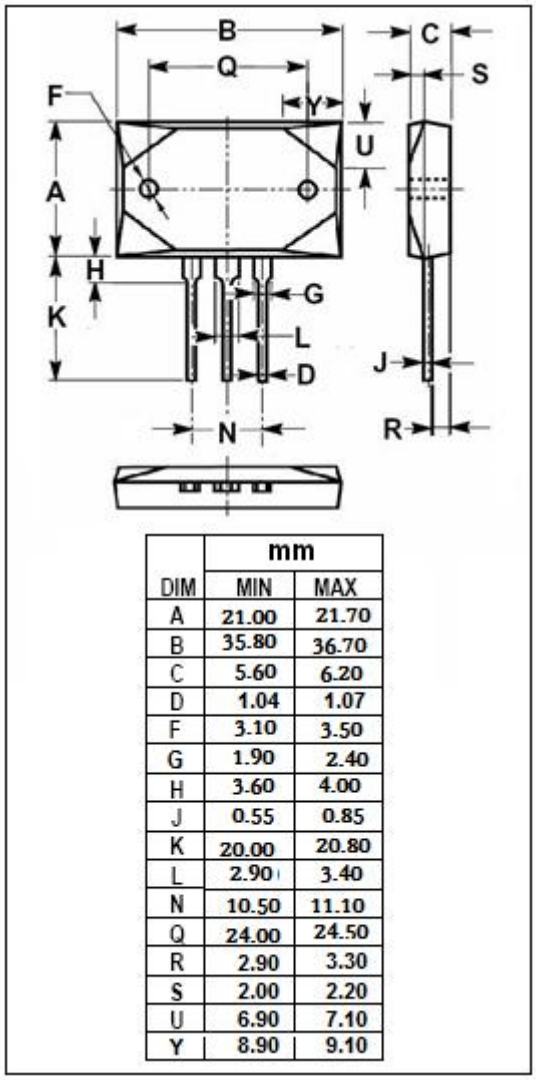


DESCRIPTION

- High Collector-Emitter Breakdown Voltage- $V_{(BR)CEO}$= 230V(Min)
- Good Linearity of h_{FE}
- Complement to Type 2SA1295
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for audio and general purpose applications.



DIM	mm MIN	mm MAX
A	21.00	21.70
B	35.80	36.70
C	5.60	6.20
D	1.04	1.07
F	3.10	3.50
G	1.90	2.40
H	3.60	4.00
J	0.55	0.85
K	20.00	20.80
L	2.90	3.40
N	10.50	11.10
Q	24.00	24.50
R	2.90	3.30
S	2.00	2.20
U	6.90	7.10
Y	8.90	9.10

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	230	V
V_{CEO}	Collector-Emitter Voltage	230	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	17	A
I_B	Base Current-Continuous	5	A
P_C	Collector Power Dissipation @ T_C=25℃	200	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 25mA ; I_B= 0	230			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 5A; I_B= 0.5A			2.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 230V; I_E= 0			100	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			100	μA
h_{FE}	DC Current Gain	I_C= 5A; V_{CE}= 4V	50		140	
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= 10V;f_{test}= 1.0MHz		250		pF
f_T	Current-Gain—Bandwidth Product	I_E= -2A; V_{CE}= 12V	30			MHz
Switching times						
t_{on}	Turn-on Time	I_C= 5A ,R_L= 12Ω , I_{B1}= -I_{B2}= 0.5A,V_{CC}= 60V		0.3		μs
t_{stg}	Storage Time			2.4		μs
t_f	Fall Time			0.5		μs

◆ h_{FE} Classifications

O	Y
50-100	70-140